

**1N38**  
**GOLD BONDED GERMANIUM DIODE**

**FEATURES**

Low forward voltage drop—low power consumption  
Thirty years of proven reliability—one million hours mean time between failures (MTBF)  
Very low noise level  
Metallurgically bonded

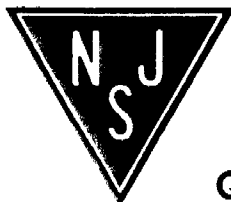
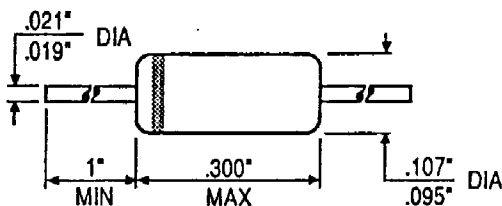
**ABSOLUTE MAXIMUM RATINGS** (at 25 °C, unless otherwise specified)

Peak Inverse Voltage 100 Volts  
Peak Forward Current 500 mA  
Operating Temperature Range - 65 °C to 85 °C  
Average Power Dissipation 80 mW

**ELECTRICAL CHARACTERISTICS**

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	100		V	25 °C
Reverse Current	I <sub>r</sub>	10 V		25	μA	25 °C
Forward Voltage	V <sub>f</sub>	7.5 mA		1	V	25 °C

**MECHANICAL**



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**Quality Semi-Conductors**